What is Claimed is:

1.   A   method   for   forming   a   transistor   of   a
semiconductor device, comprising the steps of:

5   forming   a   gate   electrode   on   a   semiconductor
substrate;

ion-implanting   impurities   into   the   semiconductor
substrate   using   the   gate   electrode   as   a   mask   to   form   a
source/drain junction region by;

10   forming an oxide film on the resulting structure at a
temperature below 700°C; and

forming   a   nitride   film   spacer   on   a   sidewall   of   the
gate electrode.

15   2.   The   method   according   to   claim   1,   wherein   the
step of ion-implanting impurities comprises ion-implanting
$_{31}$P   at   an   energy   ranging   from   10   to   35KeV   and   at   a   dose
ranging from 1.0E12 to 5.0E13 ions/cm^2.

20   3.   The   method   according   to   claim   1,   wherein   the
step   of   ion-implanting   process   impurities   comprises   ion-
implanting $_{75}$As   at   an   energy   ranging   from   15   to   70KeV   and
at   a   dose   ranging   from   1.0E12   to   5.0E13   ions/cm^2.

4.   The method according to claim 1, wherein the ion-implanting process is performed using a single-type equipment without wafer tilt and rotation.

5.   The method according to claim 1, wherein the ion-implanting process is performed with a tilt of 1° and in a bi-rotation or a quardruple-rotation configuration using a single-type equipment.

6.   The method according to claim 1, wherein the step of forming an oxide film is a CVD or a PVD process.

7.   The method according to claim 1, wherein the step of forming an oxide film comprises depositing the oxide film via a CVD or a PVD process performed at a temperature below 600°C, and performing thermal treatment of the semiconductor substrate at a temperature ranging from 600 to 700°C under a nitrogen gas atmosphere.

8.   The method according to claim 7, wherein the thermal treatment is a rapid thermal treatment performed for 1 to 5 minutes or a thermal treatment performed in a furnace for a time period ranging from 1 minutes to 6 hours.

9. The method according to claim 7, wherein the thermal treatment is in a furnace for 1 minutes to 6 hours.